



May 2000

QFET™

FQS4410

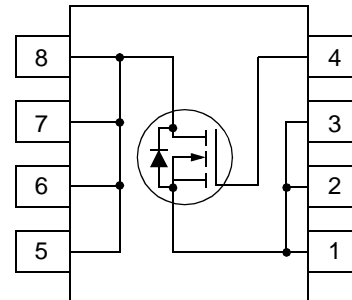
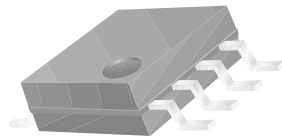
Single N-Channel, Logic Level, Power MOSFET

General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for low voltage applications such as DC/DC converters, high efficiency switching for power management in portable and battery operated products.

Features

- 10A, 30V, $R_{DS(on)} = 0.0135\Omega @ V_{GS} = 10V$
- Low gate charge (typical 21 nC)
- Low Crss (typical 145 pF)
- Fast switching
- Improved dv/dt capability
- 175°C maximum junction temperature rating



Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	FQS4410	Units
V _{DSS}	Drain-Source Voltage	30	V
I _D	Drain Current - Continuous (T _C = 25°C)	10	A
	- Continuous (T _C = 70°C)	8	A
I _{DM}	Drain Current - Pulsed (Note 1)	50	A
V _{GSS}	Gate-Source Voltage	± 20	V
dv/dt	Peak Diode Recovery dv/dt (Note 3)	7.0	V/ns
P _D	Power Dissipation (T _C = 25°C)	2.5	W
	Linear Derating Factor	0.02	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +175	°C

Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
R _{θJA}	Thermal Resistance, Junction-to-Ambient	--	50	°C/W

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	30	--	--	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C	--	0.03	--	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 24\text{ V}, T_C = 125^\circ\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1.0	--	2.5	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 10\text{ A}$	--	--	0.0135	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 5\text{ A}$ (Note 4)	--	--	0.02	
g_{FS}	Forward Transconductance	$V_{DS} = 10\text{ V}, I_D = 5\text{ A}$	--	16	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	980	1280	pF
C_{oss}	Output Capacitance		--	590	770	pF
C_{riss}	Reverse Transfer Capacitance		--	145	190	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15\text{ V}, I_D = 5\text{ A},$ $R_G = 50\ \Omega$ (Note 4, 5)	--	30	70	ns
t_r	Turn-On Rise Time		--	165	340	ns
$t_{d(off)}$	Turn-Off Delay Time		--	65	140	ns
t_f	Turn-Off Fall Time		--	110	230	ns
Q_g	Total Gate Charge	$V_{DS} = 24\text{ V}, I_D = 10\text{ A},$ $V_{GS} = 5\text{ V}$ (Note 4, 5)	--	21	28	nC
Q_{gs}	Gate-Source Charge		--	4.2	--	nC
Q_{gd}	Gate-Drain Charge		--	12	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current	--	--	2.3	A	
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	50	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 2.3\text{ A}$	--	--	1.1	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 24\text{ A},$ (Note 4)	--	45	--	ns
Q_{rr}	Reverse Recovery Charge	$di_F / dt = 100\text{ A}/\mu\text{s}$	--	45	--	nC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 3\text{ mH}, I_{AS} = 10\text{ A}, V_{DD} = 15\text{ V}, R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 10\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\ \mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

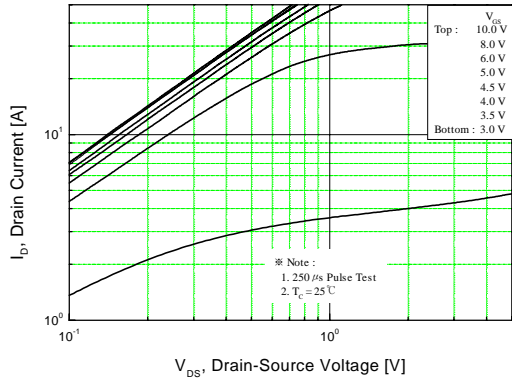


Figure 1. Output Characteristics

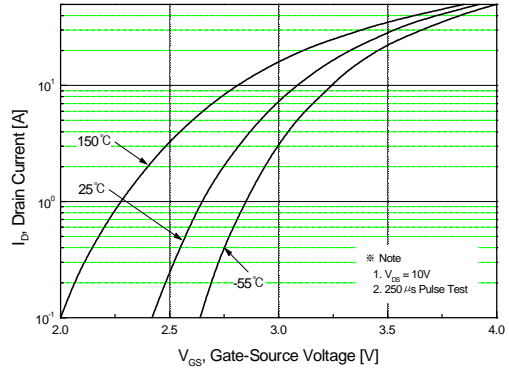


Figure 2. Transfer Characteristics

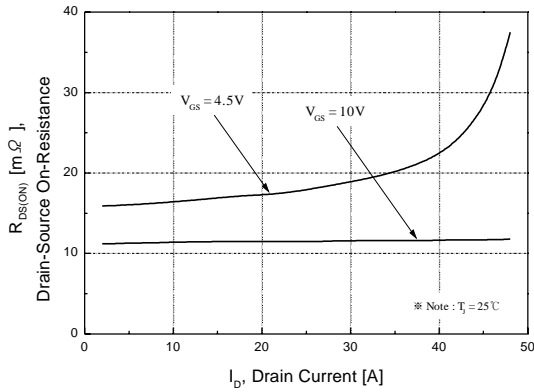


Figure 3. On-Resistance Variation vs. Drain Current

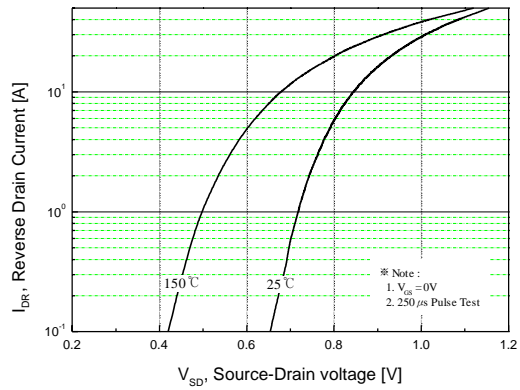


Figure 4. Source-Drain Diode Forward Voltage

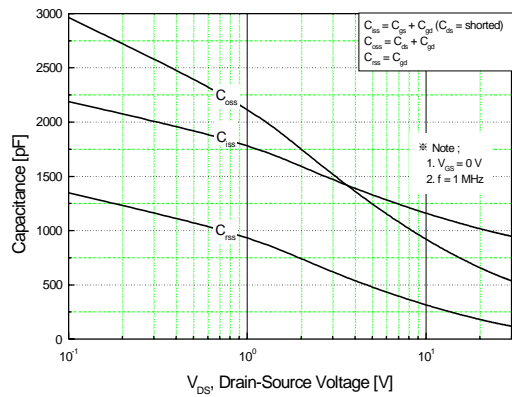


Figure 5. Capacitance vs. Drain-Source Voltage

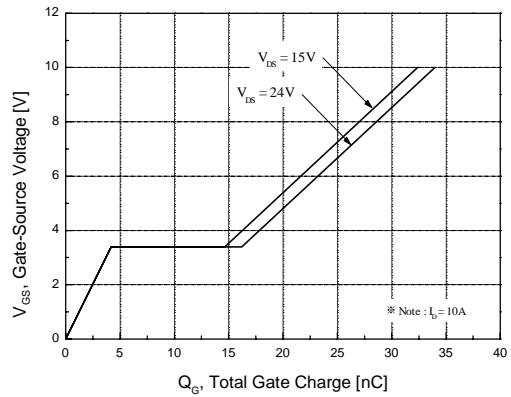


Figure 6. Gate Charge vs. Gate-Source Voltage

Typical Characteristics (Continued)

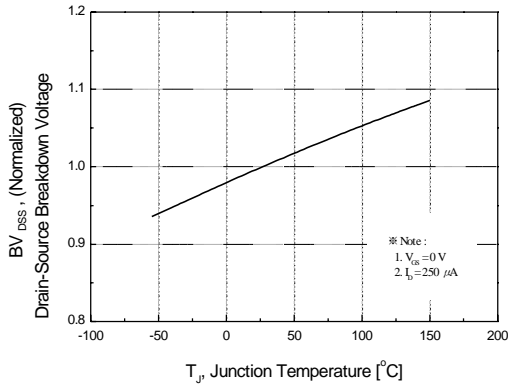


Figure 7. Breakdown Voltage vs. Temperature

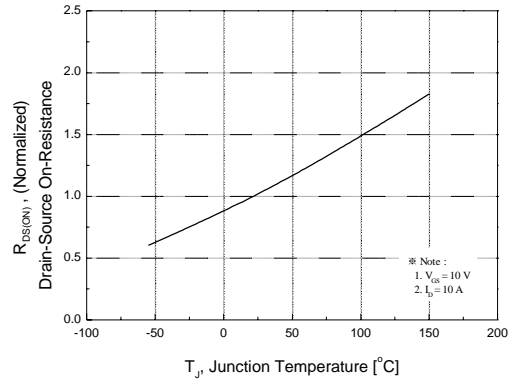


Figure 8. On-Resistance vs. Temperature

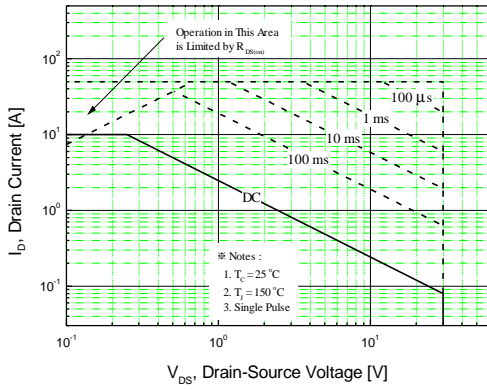


Figure 9. Maximum Safe Operating Area

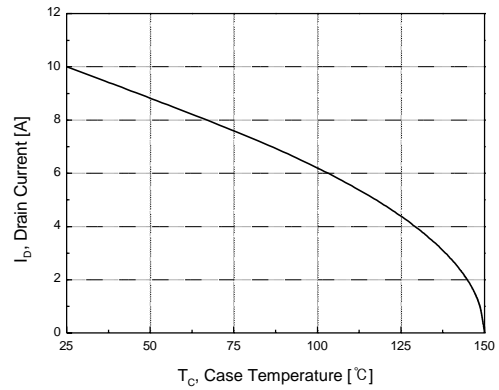


Figure 10. Maximum Drain Current vs. Case Temperature

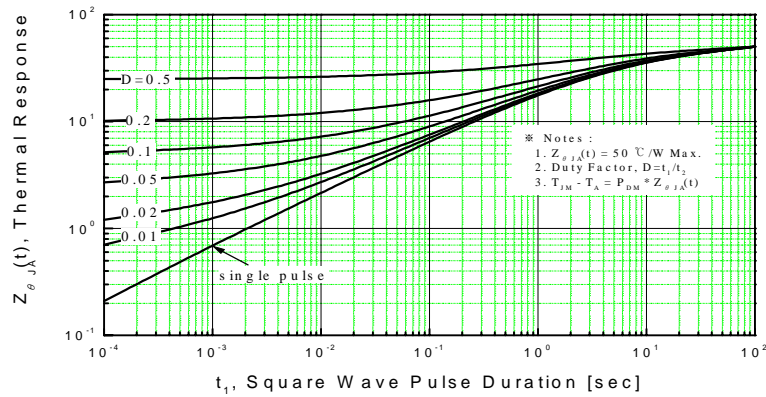
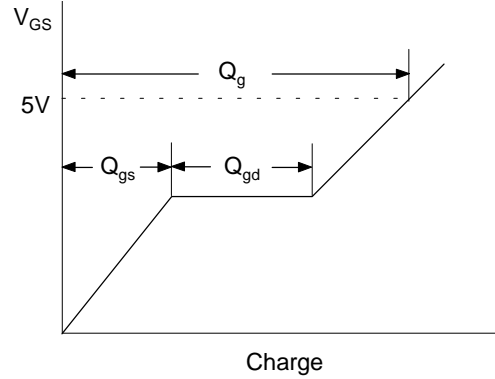
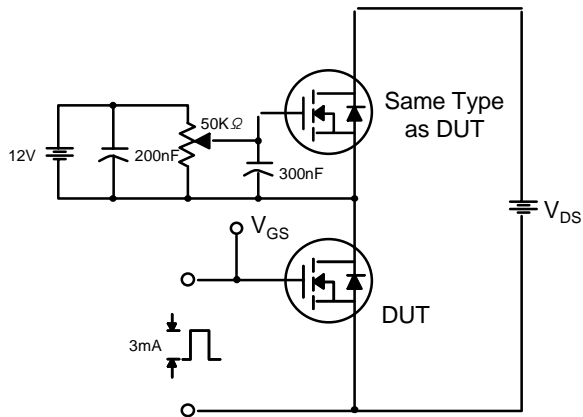
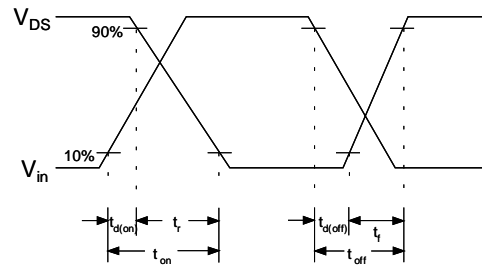
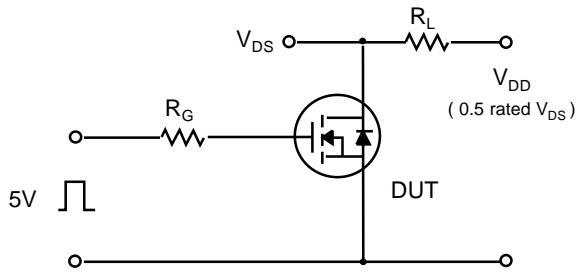


Figure 11. Thermal Response

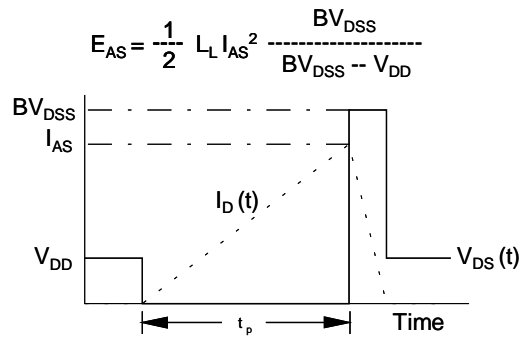
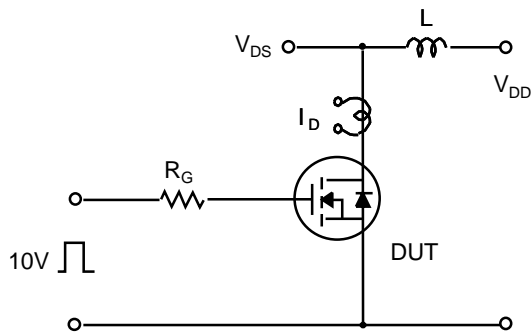
Gate Charge Test Circuit & Waveform



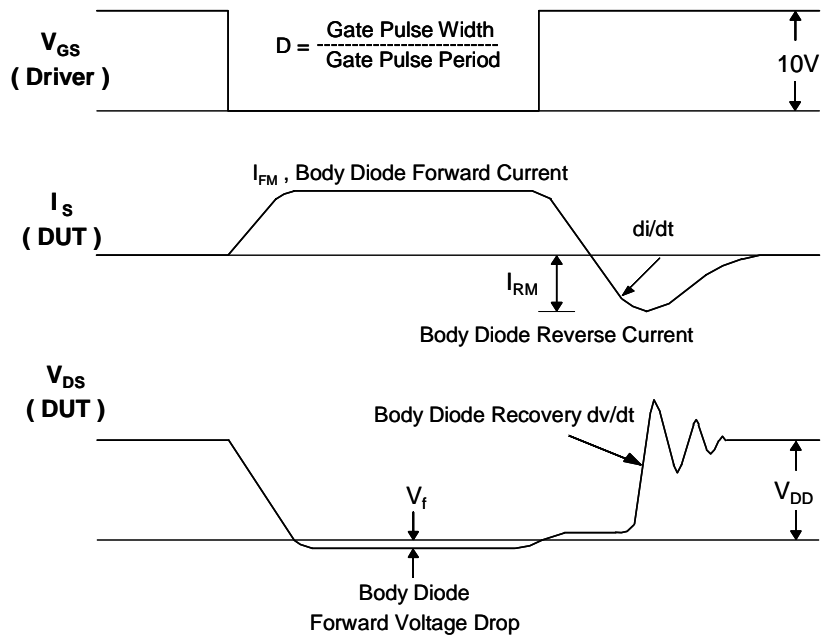
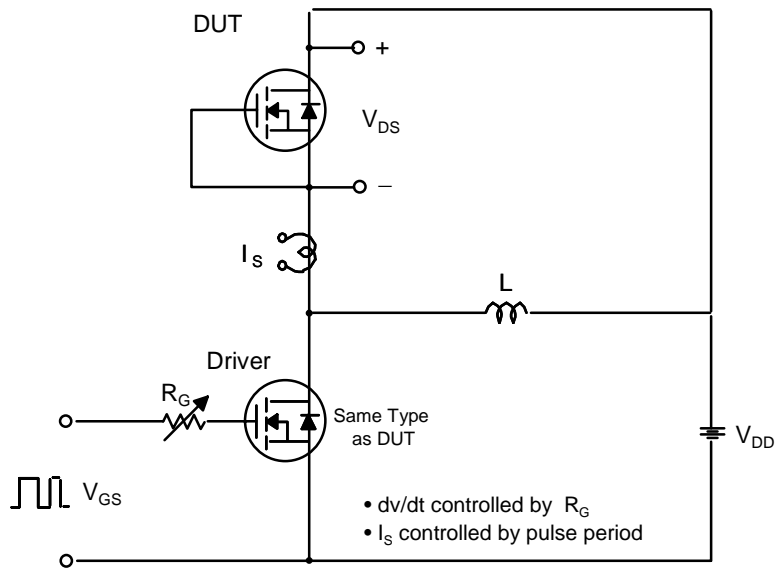
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

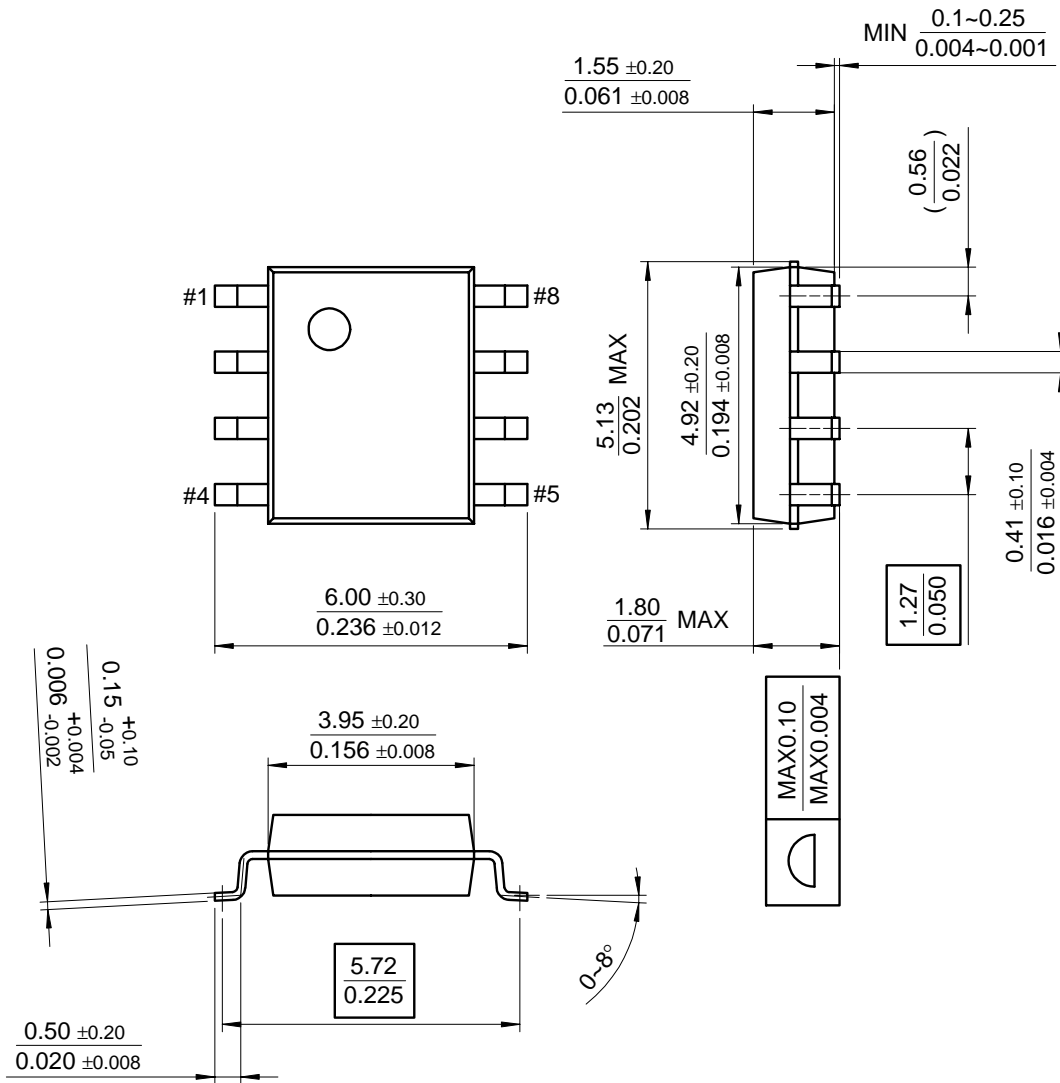


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Dimensions

8-SOP



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